

Abstract of the Disclosure:

During a selective oxidation of gate structures that includes a polycrystalline silicon layer and a tungsten layer, which is known per se, a vapor deposition of tungsten oxide is
5 prevented or at least greatly reduced by a special process.
The gate structure is acted on by a hydrogen-containing, nonaqueous inert gas before and, if appropriate, after a treatment step with a hydrogen/water mixture.

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